

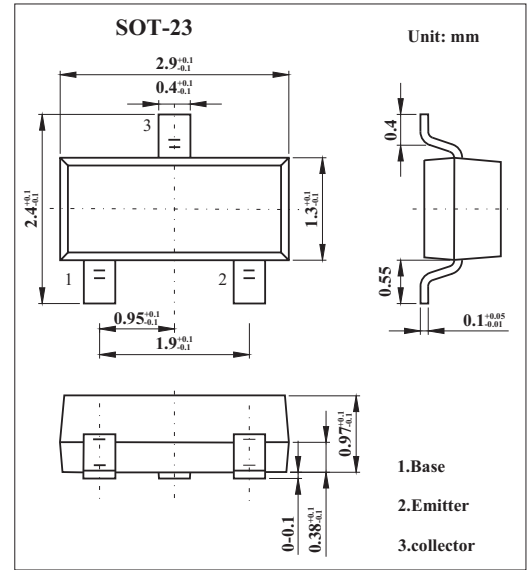
SOT-23 Plastic-Encapsulate Transistors

Features

- High collector current.
- High current gain.
- Low collector-emitter saturation voltage.
- PNP Silicon AF Transistors

MECHANICAL DATA

- Case style: SOT-23 molded plastic
- Mounting position: any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-30	V
Collector-emitter voltage	V _{CEO}	-25	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current (DC)	I _c	-800	mA
power dissipation	P _D	310	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-65 to +150	°C

PACKAGE INFORMATION

Device	Package	Shipping
BC808	SOT-23	3000/Tape&Reel

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-to-baser breakdown voltage	V _{CB0}	I _c = -10 μA, V _{BE} = 0	-30			V
Collector-to-emitter breakdown voltage	V _{CEO}	I _c = -10 mA, I _B = 0	-25			V
Emitter-to-base breakdown voltage	V _{EBO}	I _E = -10 μA, I _c = 0	-5			V
Collector cutoff current	I _{CES}	V _{CB} = -25 V, V _{BE} = 0			-100	nA
Emitter cutoff current	I _{EBO}	V _{EB} = -4 V, I _c = 0			-100	nA
DC current gain *	h _{FE}	I _c = -100 mA, V _{CE} = -1 V	100		630	
		I _c = -300 mA, V _{CE} = -1 V	60			
Collector saturation voltage *	V _{CE(sat)}	I _c = -500 mA, I _B = -50 mA			-0.7	V
Base emitter on voltage	V _{BE(on)}	V _{CE} = -1V, I _c = 300mA			-1.2	V
Output Capacitance	C _{ob}	V _{CB} = -10V, f = 1MHz			12	pF
Transition frequency	f _t	I _c = -10 mA, V _{CE} = -5 V, f = 50 MHz		100		MHz

* Pulsed: PW ≤ 350 μs, duty cycle ≤ 2%

Marking

NO.	KC808-16	KC808-25	KC808-40
Marking	9GA	9GB	9GC
h _{FE}	100 ~ 250	160 ~ 400	250 ~ 630